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(54) **VOLTAGE BUFFER**

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(57) **ABSTRACT**

In an example, a circuit includes a first field-effect transistor (FET) having a gate and first and second terminals. The circuit includes a second FET having a gate and first and second terminals, the second terminals of the first and second FETs coupled together. The circuit includes a first boosted follower coupled to the gate of the first FET and includes a second boosted follower coupled to the gate of the second FET. A third FET is coupled to the first boosted follower and the second voltage terminal and configured to turn off the first boosted follower responsive to a first level of an output voltage. A fourth FET is coupled to the second boosted follower and the first voltage terminal and configured to turn off the second boosted follower responsive to a second level of the output voltage.